

FEATURES:

- 0.5 MICRON CMOS Technology
- Typical $t_{sk(o)}$ (Output Skew) < 250ps
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- $V_{CC} = 3.3V \pm 0.3V$, Normal Range
- $V_{CC} = 2.7V$ to $3.6V$, Extended Range
- $V_{CC} = 2.5V \pm 0.2V$
- CMOS power levels ($0.4\mu W$ typ. static)
- Rail-to-Rail output swing for increased noise margin
- Available in TSSOP package

DRIVE FEATURES:

- Balanced Output Drivers: $\pm 12mA$
- Low switching noise

APPLICATIONS:

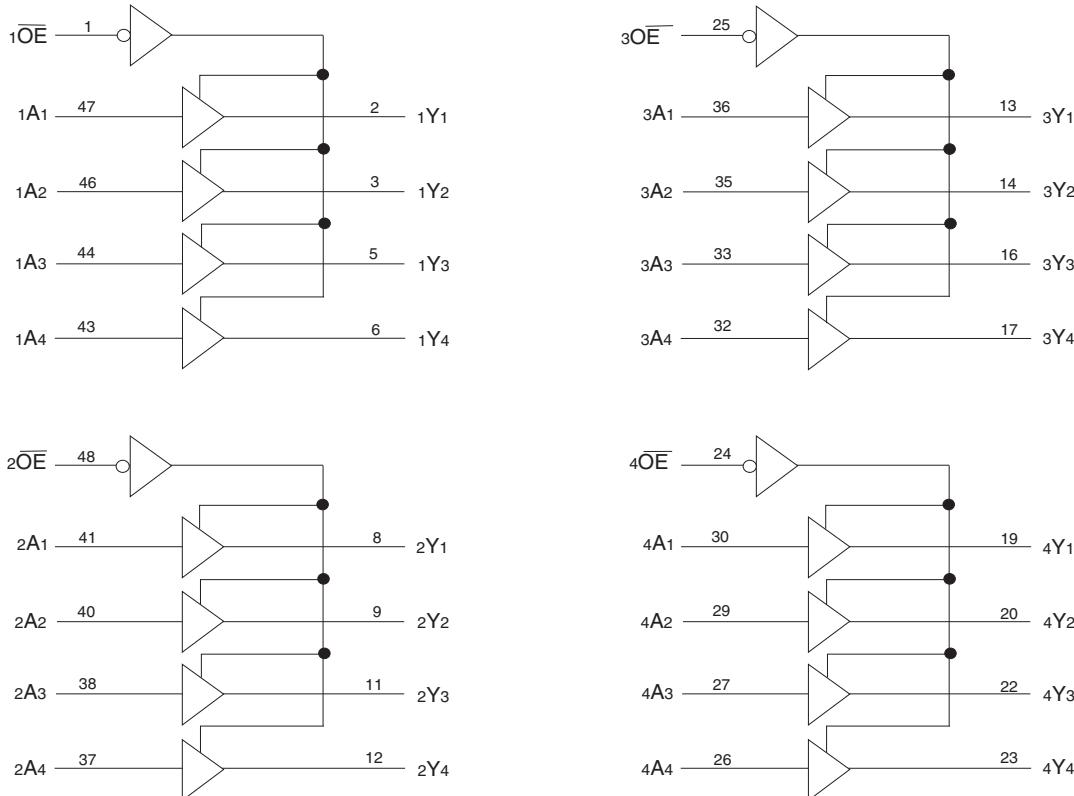
- 3.3V high speed systems
- 3.3V and lower voltage computing systems

DESCRIPTION:

This 16-bit buffer/driver is built using advanced dual metal CMOS technology. The ALVCH162244 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable (\overline{OE}) inputs.

The ALVCH162244 has series resistors in the device output structure which will significantly reduce line noise when used with light loads. This driver has been designed to drive $\pm 12mA$ at the designated threshold levels.

The ALVCH162244 has "bus-hold" which retains the inputs' last state whenever the input bus goes to a high impedance. This prevents floating inputs and eliminates the need for pull-up/down resistors.

FUNCTIONAL BLOCK DIAGRAM

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INDUSTRIAL TEMPERATURE RANGE

SEPTEMBER 2016

PIN CONFIGURATION

1 \bar{OE}	1	48	2 \bar{OE}
1Y1	2	47	1A1
1Y2	3	46	1A2
GND	4	45	GND
1Y3	5	44	1A3
1Y4	6	43	1A4
VCC	7	42	VCC
2Y1	8	41	2A1
2Y2	9	40	2A2
GND	10	39	GND
2Y3	11	38	2A3
2Y4	12	37	2A4
3Y1	13	36	3A1
3Y2	14	35	3A2
GND	15	34	GND
3Y3	16	33	3A3
3Y4	17	32	3A4
VCC	18	31	VCC
4Y1	19	30	4A1
4Y2	20	29	4A2
GND	21	28	GND
4Y3	22	27	4A3
4Y4	23	26	4A4
4 \bar{OE}	24	25	3 \bar{OE}

TSSOP
TOP VIEWABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
TSTG	Storage Temperature	-65 to +150	°C
I _{OUT}	DC Output Current	-50 to +50	mA
I _{IK}	Continuous Clamp Current, V _I < 0 or V _I > V _{CC}	±50	mA
I _{OK}	Continuous Clamp Current, V _O < 0	-50	mA
I _{CC}	Continuous Current through each V _{CC} or GND	±100	mA
I _{SS}			

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. V_{CC} terminals.
3. All terminals except V_{CC}.

CAPACITANCE (T_A = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	5	7	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	7	9	pF
C _{I/O}	I/O Port Capacitance	V _{IN} = 0V	7	9	pF

NOTE:

1. As applicable to the device type.

PIN DESCRIPTION

Pin Names	Description
x \bar{OE}	3-State Output Enable Inputs (Active LOW)
xA _x	Data Inputs ⁽¹⁾
xY _x	3-State Outputs

NOTE:

1. These pins have "Bus-Hold". All other pins are standard inputs, outputs, or I/Os.

FUNCTION TABLE (EACH 4-BIT BUFFER)⁽¹⁾

Inputs		Outputs
x \bar{OE}	xA _x	xY _x
L	H	H
L	L	L
H	X	Z

NOTE:

1. H = HIGH Voltage Level
X = Don't Care
L = LOW Voltage Level
Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Operating Condition: $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$

Symbol	Parameter	Test Conditions		Min.	Typ. ⁽¹⁾	Max.	Unit
V _{IH}	Input HIGH Voltage Level	V _{CC} = 2.3V to 2.7V		1.7	—	—	V
		V _{CC} = 2.7V to 3.6V		2	—	—	
V _{IL}	Input LOW Voltage Level	V _{CC} = 2.3V to 2.7V		—	—	0.7	V
		V _{CC} = 2.7V to 3.6V		—	—	0.8	
I _{IH}	Input HIGH Current	V _{CC} = 3.6V	V _I = V _{CC}	—	—	± 5	μA
I _{IL}	Input LOW Current	V _{CC} = 3.6V	V _I = GND	—	—	± 5	μA
I _{OZH}	High Impedance Output Current (3-State Output pins)	V _{CC} = 3.6V	V _O = V _{CC}	—	—	± 10	μA
			V _O = GND	—	—	± 10	
V _{IK}	Clamp Diode Voltage	V _{CC} = 2.3V, I _{IN} = -18mA		—	-0.7	-1.2	V
V _H	Input Hysteresis	V _{CC} = 3.3V		—	100	—	mV
I _{CCL} I _{CCH} I _{CZZ}	Quiescent Power Supply Current	V _{CC} = 3.6V V _{IN} = GND or V _{CC}		—	0.1	40	μA
ΔI_{CC}	Quiescent Power Supply Current Variation	One input at V _{CC} - 0.6V, other inputs at V _{CC} or GND		—	—	750	μA

NOTE:

1. Typical values are at V_{CC} = 3.3V, $+25^\circ\text{C}$ ambient.

BUS-HOLD CHARACTERISTICS

Symbol	Parameter ⁽¹⁾	Test Conditions		Min.	Typ. ⁽²⁾	Max.	Unit
I _{BHH} I _{BHL}	Bus-Hold Input Sustain Current	V _{CC} = 3V	V _I = 2V	-75	—	—	μA
			V _I = 0.8V	75	—	—	
I _{BHH} I _{BHL}	Bus-Hold Input Sustain Current	V _{CC} = 2.3V	V _I = 1.7V	-45	—	—	μA
			V _I = 0.7V	45	—	—	
I _{BHHO} I _{BHLO}	Bus-Hold Input Overdrive Current	V _{CC} = 3.6V	V _I = 0 to 3.6V	—	—	± 500	μA

NOTES:

1. Pins with Bus-Hold are identified in the pin description.

2. Typical values are at V_{CC} = 3.3V, $+25^\circ\text{C}$ ambient.

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Max.	Unit
VOH	Output HIGH Voltage	Vcc = 2.3V to 3.6V	IOH = - 0.1mA	Vcc - 0.2	—	V
		Vcc = 2.3V	IOH = - 4mA	1.9	—	
			IOH = - 6mA	1.7	—	
		Vcc = 2.7V	IOH = - 4mA	2.2	—	
			IOH = - 8mA	2	—	
		Vcc = 3V	IOH = - 6mA	2.4	—	
			IOH = - 12mA	2	—	
		Vcc = 2.3V to 3.6V	IOH = 0.1mA	—	0.2	V
			IOH = 4mA	—	0.4	
			IOH = 6mA	—	0.55	
			IOH = 4mA	—	0.4	
			IOH = 8mA	—	0.6	
			IOH = 6mA	—	0.55	
			IOH = 12mA	—	0.8	

NOTE:

1. V_{IH} and V_{IL} must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate Vcc range.
 $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$.

OPERATING CHARACTERISTICS, $T_A = 25^\circ\text{C}$

Symbol	Parameter	Test Conditions	Vcc = 2.5V \pm 0.2V	Vcc = 3.3V \pm 0.3V	Unit
			Typical	Typical	
CPD	Power Dissipation Capacitance Outputs enabled	CL = 0pF, f = 10Mhz	16	19	pF
	Power Dissipation Capacitance Outputs disabled		4	5	

SWITCHING CHARACTERISTICS⁽¹⁾

Symbol	Parameter	Vcc = 2.5V \pm 0.2V		Vcc = 2.7V		Vcc = 3.3V \pm 0.3V		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t _{PLH}	Propagation Delay xAx to xYx	1	4.9	—	4.7	1	4.2	ns
t _{PHL}	Output Enable Time x \overline{OE} to xYx	1	6.8	—	6.7	1	5.6	ns
t _{PZH}	Output Disable Time x \overline{OE} to xYx	1	6.3	—	5.7	1	5.5	ns
t _{PLZ}	Output Skew ⁽²⁾	—	—	—	—	—	500	ps

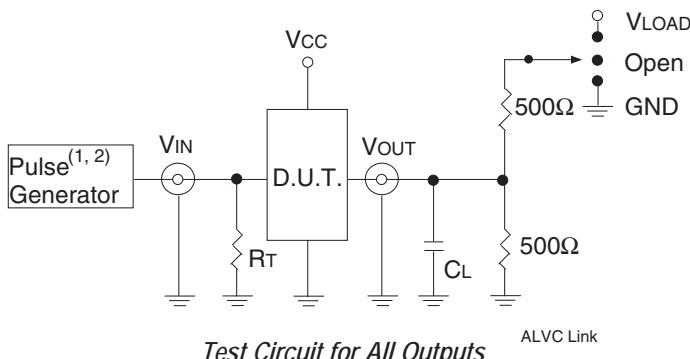
NOTES:

- See TEST CIRCUITS AND WAVEFORMS. $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$.
- Skew between any two outputs of the same package and switching in the same direction.

TEST CIRCUITS AND WAVEFORMS

TEST CONDITIONS

Symbol	$V_{CC}^{(1)} = 3.3V \pm 0.3V$	$V_{CC}^{(1)} = 2.7V$	$V_{CC}^{(2)} = 2.5V \pm 0.2V$	Unit
V_{LOAD}	6	6	$2 \times V_{CC}$	V
V_{IH}	2.7	2.7	V_{CC}	V
V_T	1.5	1.5	$V_{CC} / 2$	V
V_{LZ}	300	300	150	mV
V_{HZ}	300	300	150	mV
C_L	50	50	30	pF



Test Circuit for All Outputs

DEFINITIONS:

C_L = Load capacitance: includes jig and probe capacitance.

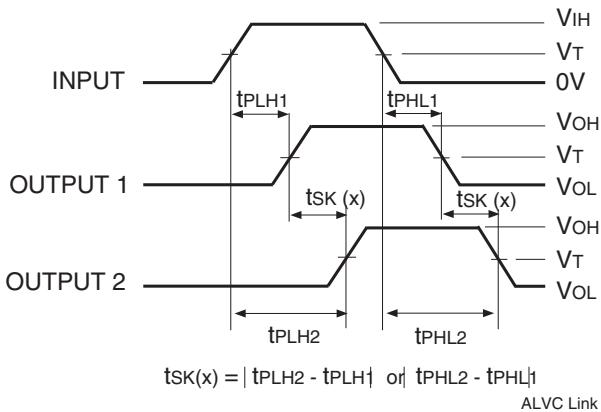
R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

NOTES:

1. Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; t_f $\leq 2.5\text{ns}$; t_r $\leq 2.5\text{ns}$.
2. Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; t_f $\leq 2\text{ns}$; t_r $\leq 2\text{ns}$.

SWITCH POSITION

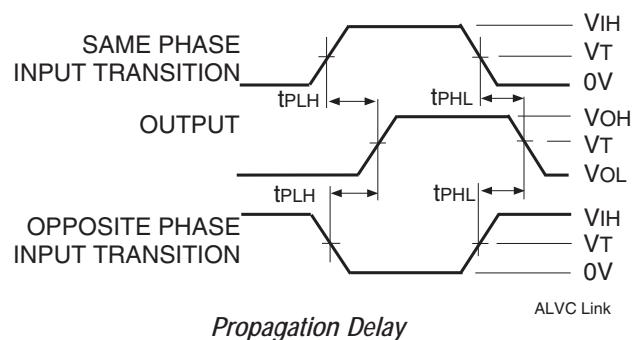
Test	Switch
Open Drain	
Disable Low	V _{LOAD}
Enable Low	
Disable High	GND
Enable High	
All Other Tests	Open



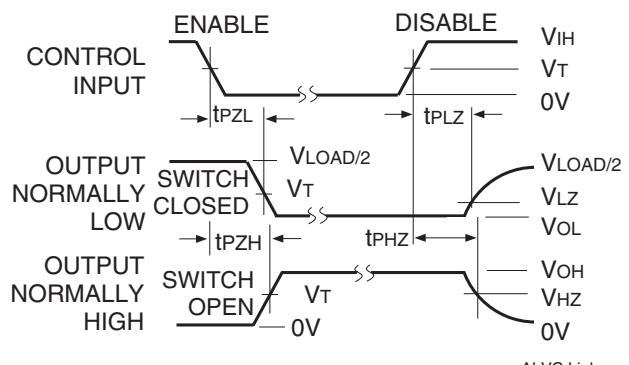
Output Skew - t_{SK(x)}

NOTES:

1. For t_{SK(o)} OUTPUT1 and OUTPUT2 are any two outputs.
2. For t_{SK(b)} OUTPUT1 and OUTPUT2 are in the same bank.



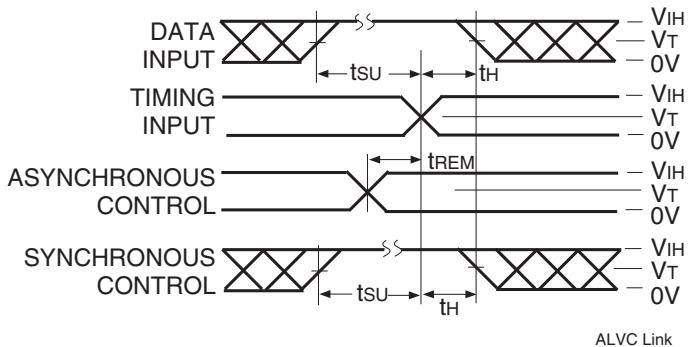
Propagation Delay



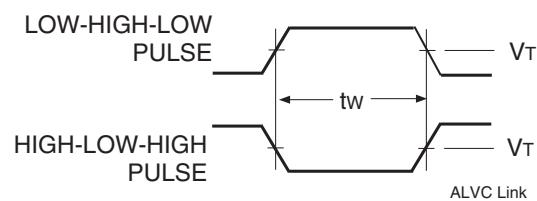
Enable and Disable Times

NOTE:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.

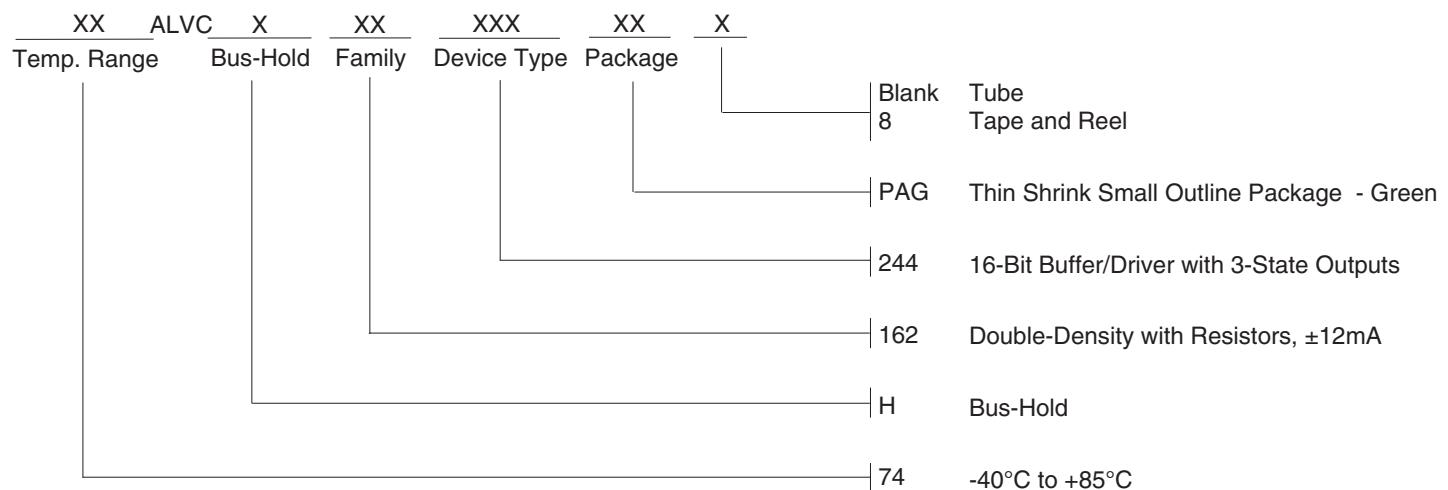


Set-up, Hold, and Release Times



Pulse Width

ORDERING INFORMATION



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